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DATE MAILED:

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR			ATTORNEY DOCKET NO.
09/502,729	02/11/00	COHEN		S	Y0999-573
Г		talann zon t	一	EXAMINER	
MMC2/0814 ' Rocco S Barrese Esq				LOUIE,	W
Dilworth & Barrese				ART UNIT	PAPER NUMBER
333 Earle Ovington Boulevard Uniondale NY 11553				2814	

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

08/14/01

		Application No.	Applicant(s)
		09/502,729	COHEN ET AL.
Office Action Summary		Examiner	Art Unit
		Wai-Sing Louie	2814
Period fo	The MAILING DATE of this communication a or Reply	pp ars on the cov r sheet wi	ith the correspond nc address
- Exte after - If the - If NC - Failu - Any	ORTENED STATUTORY PERIOD FOR REP MAILING DATE OF THIS COMMUNICATION nsions of time may be available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication. Period for reply specified above is less than thirty (30) days, a report of the provided provided above is less than thirty (30) days, a report of the reply is specified above, the maximum statutory period report of the reply within the set or extended period for reply will, by statically received by the Office later than three months after the mailed patent term adjustment. See 37 CFR 1.704(b).	I. 1.136(a). In no event, however, may a reply within the statutory minimum of thirt d will apply and will expire SIX (6) MON the cause the application to become AB.	eply be timely filed y (30) days will be considered timely. THS from the mailing date of this communication.
1)	Responsive to communication(s) filed on		
2a) <u></u> □	This action is FINAL . 2b)⊠ 1	his action is non-final.	
3)	Since this application is in condition for allow closed in accordance with the practice under	vance except for formal mat r <i>Ex parte Quayle</i> , 1935 C.[ters, prosecution as to the merits is D. 11, 453 O.G. 213.
Dispositi	on of Claims		
4)🛛	Claim(s) 1-34 is/are pending in the application	on.	
	4a) Of the above claim(s) <u>17-34</u> is/are withdra	awn from consideration.	
	Claim(s) is/are allowed.		
6)⊠	Claim(s) <u>1-16</u> is/are rejected.		
7)	Claim(s) is/are objected to.		
8)[Claim(s) are subject to restriction and/	or election requirement.	
	on Papers	·	
9)[] 7	he specification is objected to by the Examin	er.	
	he drawing(s) filed on is/are: a)☐ acce		e Examiner.
	Applicant may not request that any objection to the		
11)□ T	he proposed drawing correction filed on		
	If approved, corrected drawings are required in re		
12)[] T	he oath or declaration is objected to by the E	xaminer.	
Priority u	nder 35 U.S.C. §§ 119 and 120		
13) 🗌 .	Acknowledgment is made of a claim for foreig	n priority under 35 U.S.C. §	119(a)-(d) or (f).
a)[All b) Some * c) None of:		
	1. Certified copies of the priority documen	ts have been received.	
2	2. Certified copies of the priority documen	ts have been received in Ap	plication No
	B. Copies of the certified copies of the price application from the International Buse the attached detailed Office action for a list	reau (PCT Rule 17.2(a))	_
	knowledgment is made of a claim for domest		
	☐ The translation of the foreign language pro		
15) 🗌 Ad	cknowledgment is made of a claim for domest	ic priority under 35 U.S.C. 8	हा received. § 120 and/or 121
Attachment(, , ,	J := 5 =
2) 🔲 Notice	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-948) ation Disclosure Statement(s) (PTO-1449) Paper No(s) _	5) Notice of Info	ormal Patent Application (PTO-152)
Patent and Trac TO-326 (Rev.	****	ction Summary	Part of Paper No. 5

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DETAILED ACTION

1. Restriction to one of the following inventions is required under 35 U.S.C. 121:

I. Claims 1-16, drawn to a semiconductor device, classified in class 257, subclass

734.

II. Claims 17-34, drawn to the method of making the semiconductor device,

classified in class 438, subclass 624.

The inventions are distinct, each from the other because of the following reasons:

Inventions Group I and Group II are related as process of making and product made. The inventions are distinct if either or both of the following can be shown: (1) that the process as claimed can be used to make other and materially different product or (2) that the product as claimed can be made by another and materially different process (MPEP § 806.05(f)). In the instant case, instead of forming the diffusion barrier layer by DECVD, it would be possible to form the layer with atomic layer deposition.

Because these inventions are distinct for the reasons given above and have acquired a separate status in the art as shown by their different classification, restriction for examination purposes as indicated is proper.

2. During a telephone conversation with Mr. Michael Carmen on 6/26/01 a provisional

election was made without traverse to prosecute the invention of Group I, claims 1-16.

Affirmation of this election must be made by applicant in replying to this Office action.

Claims 17-34 are withdrawn from further consideration by the examiner, 37

CFR 1.142(b), as being drawn to a non-elected invention.

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Applicant is reminded that upon the cancellation of claims to a non-elected invention, the inventorship must be amended in compliance with 37 CFR 1.48(b) if one or more of the currently named inventors is no longer an inventor of at least one claim remaining in the application. Any amendment of inventorship must be accompanied by a petition under 37 CFR 1.48(b) and by the fee required under 37 CFR 1.17(i).

Claim Rejections - 35 USC § 112

3. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1-16 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In claim 1, line 3, it is unclear what is meant by "non-uniformly distributed". If nitrogen (Silicon nitride) is "non-uniformly distributed" throughout the diffusion barrier layer, will there be any bare or thin spots on the surface? Will there be any risk of delaminating or current leakage?

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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Claims 1-16 (in so far as they are understood) are rejected under 35 U.S.C. 103(a) as being unpatentable over Grill et al. (US 6,147,009).

With regard to claims 1 to 5 and 8-11, Grill et al. disclose a diffusion barrier layer for a semiconductor device (col. 4, line 66 to col. 10, line 30 and fig. 9) having an upper surface 82 and a lower surface 62 and a central portion 84 and comprising silicon, carbon, and hydrogen (col. 5, lines 5-11). Grill et al. do not disclose the nitrogen being non-uniformly distributed throughout the diffusion barrier layer. Grill et al. disclose the cap layer (surface layer) can be suitably formed of silicon nitride, silicon carbo-oxide, and their hydrogenated compounds (col. 8, lines 17-22). This layer is formed by a mixture of silicon related materials with nitrogen concentrated in the cap layers 82 and 62 and therefore, it is obvious that nitrogen is non-uniformly distributed throughout the entire layer 44.

With regard to claim 6 and 16, Grill et al. do not disclose the carbon and the silicon in the layer is in form of silicon carbide. However, Grill et al. disclose the material is a hydrogenated oxidized silicon carbon film (col. 7, lines 44-45). Therefore, it is obvious that the silicon carbon compound is silicon carbide.

With regard to claim 7, Grill et al. disclose a semiconductor device comprising:

- A substrate 32 containing conductive element 36 (fig. 9);
- A diffusion barrier layer 44 (col. 8, lines 8-9 and fig. 9) applied to at least a portion of the substrate in contact with the conductive metal element, the diffusion barrier layer having an upper surface 82 and a lower surface 62 and a central portion 84, and comprising silicon, carbon, nitrogen and hydrogen with the

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nitrogen being non-uniformly distributed throughout the diffusion barrier layer (see discussion in claim 1 above).

With regard to claims 12 and 13, Grill et al. disclose the conductive elements 36 and 40 are made from a metal selected from the group consisting of Al and Cu (col. 7, lines 56-60).

With regard to claim 14-15, Grill et al. do not disclose the diffusion barrier layer is from about 7-120 nm or 24-68 nm. However, the temperature, power, time and thickness are considered to involve routine optimization, which has been held to be within the level of ordinary skill in the art. As noted in In re Aller, the selection of reaction parameters such as temperature and concentration, thickness etc. would have been obvious:

"Normally, it is to be expected that a change in temperature, or in thickness, or in time, would be an unpatentable modification. Under some circumstances, however, changes such as these may impart patentability to a process if the particular ranges claimed produce a new and unexpected result which is different in kind and not merely degree from the results of the prior art...such ranges are termed "critical ranges and the applicant has the burden of proving such criticality.... More particularly, where the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation."

In re Aller 105 USPQ233, 255 (CCPA 1955). See also In re Waite 77 USPQ 586 (CCPA 1948); In re Scherl 70 USPQ 204 (CCPA 1946); In re Irmscher 66 USPQ 314 (CCPA 1945); In re Norman 66 USPQ 308 (CCPA 1945); In re Swenson 56 USPQ 372 (CCPA 1942); In re Sola 25 USPQ 433 (CCPA 1935); In re Dreyfus 24 USPQ 52 (CCPA 1934).

Therefore, one of ordinary skill in the requisite art at the time the invention was made would have used any temperature, power, thickness, and time range suitable to the method in process in order to optimize the design.

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4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wai-Sing Louie whose telephone number is (703) 305-0474. The examiner can normally be reached on 7:30 AM to 4:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on (703) 306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

August 10, 2001

OLIK CHAUDHURI SUPERVISORY PATENT EXAMINER

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TECHNOLOGY CENTER 2800